



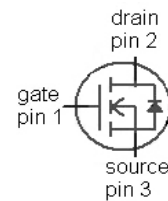
**OptiMOS® Power-Transistor**
**Features**

- For fast switching converters and sync. rectification
- N-channel enhancement - logic level
- 175 °C operating temperature
- Avalanche rated
- Pb-free lead plating, RoHS compliant

**Product Summary**

|                              |     |    |
|------------------------------|-----|----|
| $V_{DS}$                     | 60  | V  |
| $R_{DS(on),max}$ SMD version | 6.7 | mΩ |
| $I_D$                        | 80  | A  |

|                |  |  |
|----------------|--|--|
| <b>Type</b>    | IPB070N06L G   | IPP070N06L G   |
|                |  |  |
| <b>Package</b> | PG-TO263-3   | PG-TO220-3   |
| <b>Marking</b> | 070N06L  | 070N06L  |


**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol         | Conditions   | Value       | Unit  |
|-------------------------------------|----------------|--|-------------|-------|
| Continuous drain current            | $I_D$          | $T_C=25\text{ °C}^{1)}$  | 80          | A     |
|                                     |                | $T_C=100\text{ °C}$  | 80          |       |
| Pulsed drain current                | $I_{D,pulse}$  | $T_C=25\text{ °C}^{2)}$  | 320         |       |
| Avalanche energy, single pulse      | $E_{AS}$       | $I_D=80\text{ A}$ , $R_{GS}=25\text{ Ω}$   | 450         | mJ    |
| Reverse diode $dv/dt$               | $dv/dt$        | $I_D=80\text{ A}$ , $V_{DS}=48\text{ V}$ ,<br>$di/dt=200\text{ A/μs}$ ,<br>$T_{j,max}=175\text{ °C}$ | 6           | kV/μs |
| Gate source voltage                 | $V_{GS}$       |  | ±20         | V     |
| Power dissipation                   | $P_{tot}$      | $T_C=25\text{ °C}$   | 214         | W     |
| Operating and storage temperature   | $T_j, T_{stg}$ |  | -55 ... 175 | °C    |
| IEC climatic category; DIN IEC 68-1 |                |  | 55/175/56   |       |

<sup>1)</sup> Current is limited by bondwire; with an  $R_{thJC}=0.7\text{ K/W}$  the chip is able to carry 114 A.

<sup>2)</sup> See figure 3

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|                                     |            |  |   |   |     |     |
|-------------------------------------|------------|--|---|---|-----|-----|
| Thermal resistance, junction - case | $R_{thJC}$ |  | - | - | 0.7 | K/W |
| SMD version, device on PCB          | $R_{thJA}$ | minimal footprint                            | - | - | 62  |     |
|                                     |            | 6 cm <sup>2</sup> cooling area <sup>3)</sup> | - | - | 40  |     |

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

|                                  |               |  |     |      |     |               |
|----------------------------------|---------------|--|-----|------|-----|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                       | 60  | -    | -   | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=150\text{ }\mu\text{A}$                | 1.2 | 1.6  | 2   |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=60\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$  | -   | 0.01 | 1   | $\mu\text{A}$ |
|                                  |               | $V_{DS}=60\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$ | -   | 1    | 100 |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=60\text{ V}$                   | -   | 10   | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}, I_D=80\text{ A}$                      | -   | 5.8  | 7   | m $\Omega$    |
|                                  |               | $V_{GS}=4.5\text{ V}, I_D=53\text{ A}$                     | -   | 7.1  | 10  |               |
|                                  |               | $V_{GS}=10\text{ V}, I_D=80\text{ A},$<br>SMD version      |     | 5.5  | 6.7 |               |
|                                  |               | $V_{GS}=4.5\text{ V}, I_D=53\text{ A},$<br>SMD version     |     | 6.8  | 9.7 |               |
| Gate resistance                  | $R_G$         |  | -   | 1.9  | -   | $\Omega$      |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max},$<br>$I_D=80\text{ A}$       | 60  | 121  | -   | S             |

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |   |   |      |      |    |
|------------------------------|--------------|---|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=30\text{ V},$<br>$f=1\text{ MHz}$                  | - | 3200 | 4300 | pF |
| Output capacitance           | $C_{oss}$    |   | - | 750  | 1000 |    |
| Reverse transfer capacitance | $C_{rss}$    |   | - | 180  | 270  |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=30\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=80\text{ A}, R_G=2\ \Omega$ | - | 18   | 27   | ns |
| Rise time                    | $t_r$        |   | - | 35   | 52   |    |
| Turn-off delay time          | $t_{d(off)}$ |   | - | 28   | 42   |    |
| Fall time                    | $t_f$        |   | - | 31   | 47   |    |

**Gate Charge Characteristics<sup>4)</sup>**

|                          |               |  |   |     |     |    |
|--------------------------|---------------|--|---|-----|-----|----|
| Gate to source charge    | $Q_{gs}$      | $V_{DD}=30\text{ V}, I_D=80\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 12  | 15  | nC |
| Gate charge at threshold | $Q_{g(th)}$   |  | - | 5   | 7   |    |
| Gate to drain charge     | $Q_{gd}$      |  | - | 31  | 46  |    |
| Switching charge         | $Q_{sw}$      |  | - | 37  | 55  |    |
| Gate charge total        | $Q_g$         |  | - | 95  | 126 |    |
| Gate plateau voltage     | $V_{plateau}$ |  | - | 3.6 | -   | V  |
| Output charge            | $Q_{oss}$     | $V_{DD}=30\text{ V}, V_{GS}=0\text{ V}$                                    | - | 29  | 39  |    |

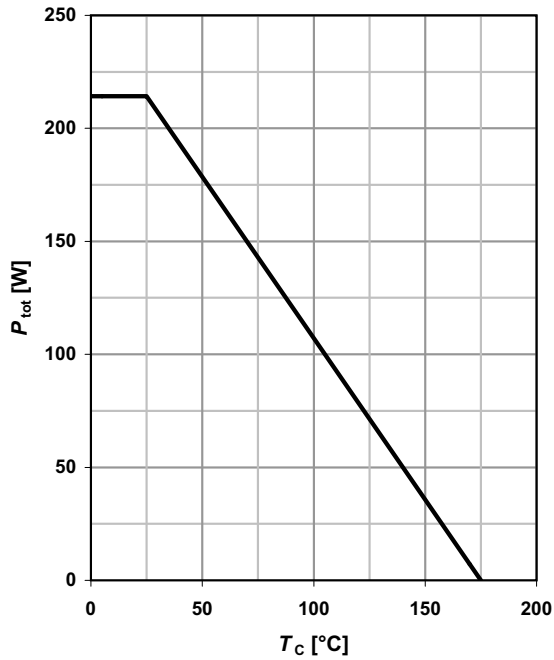
**Reverse Diode**

|                                  |               |   |   |      |     |    |
|----------------------------------|---------------|---|---|------|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ }^\circ\text{C}$  | - | -    | 80  | A  |
| Diode pulse current              | $I_{S,pulse}$ |   | - | -    | 320 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=80\text{ A},$<br>$T_j=25\text{ }^\circ\text{C}$ | - | 0.91 | 1.3 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=30\text{ V}, I_F=I_S,$<br>$di_F/dt=100\text{ A}/\mu\text{s}$       | - | 59   | 75  | ns |
| Reverse recovery charge          | $Q_{rr}$      |   | - | 80   | 100 | nC |

<sup>4)</sup> See figure 16 for gate charge parameter definition

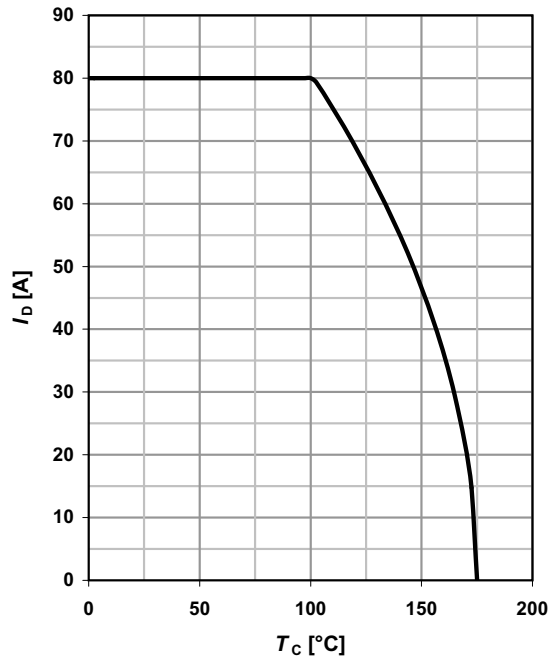
**1 Power dissipation**

$P_{tot}=f(T_C)$



**2 Drain current**

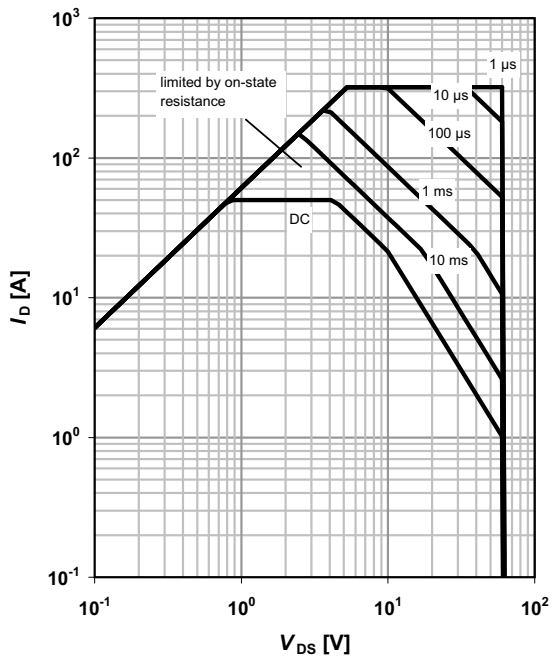
$I_D=f(T_C); V_{GS} \geq 10\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

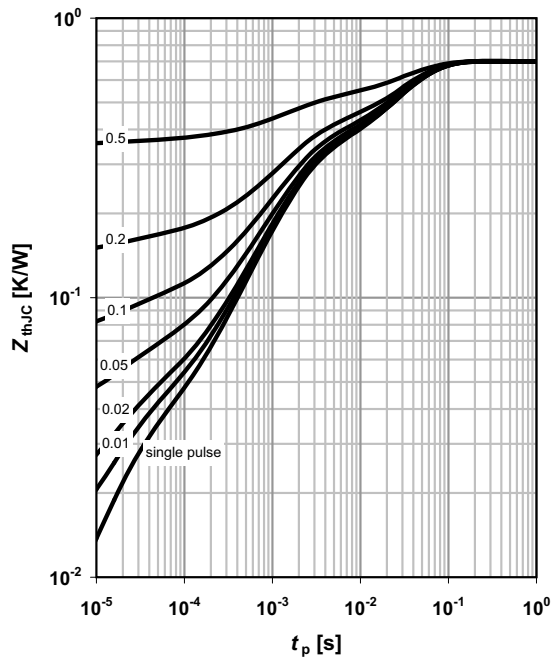
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

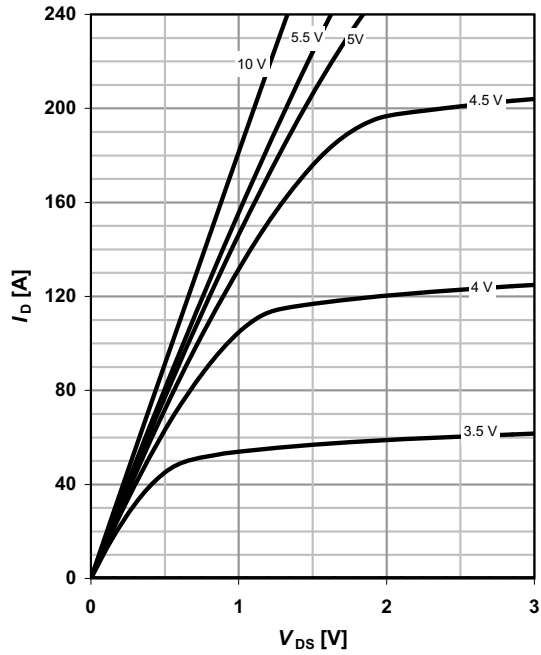
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

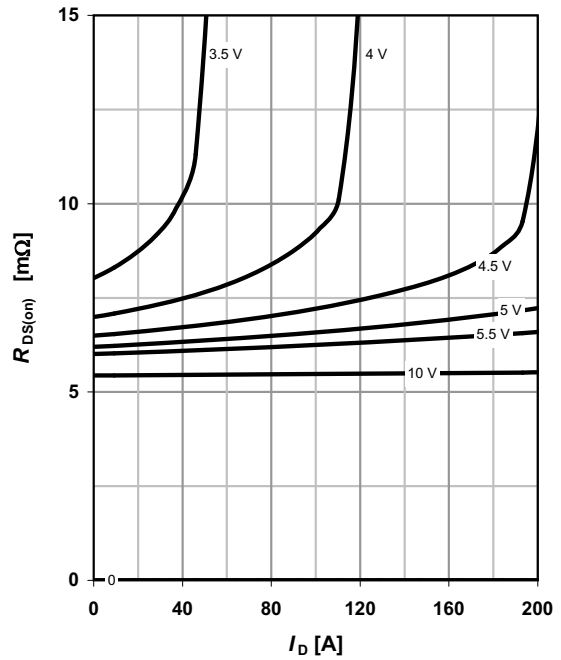
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

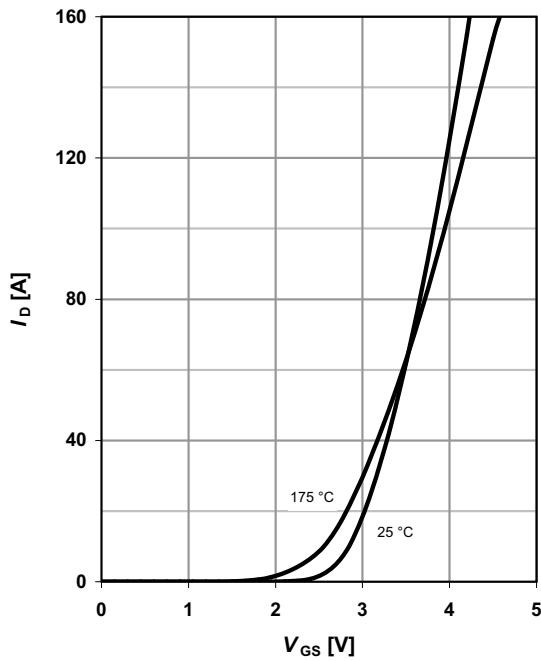
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

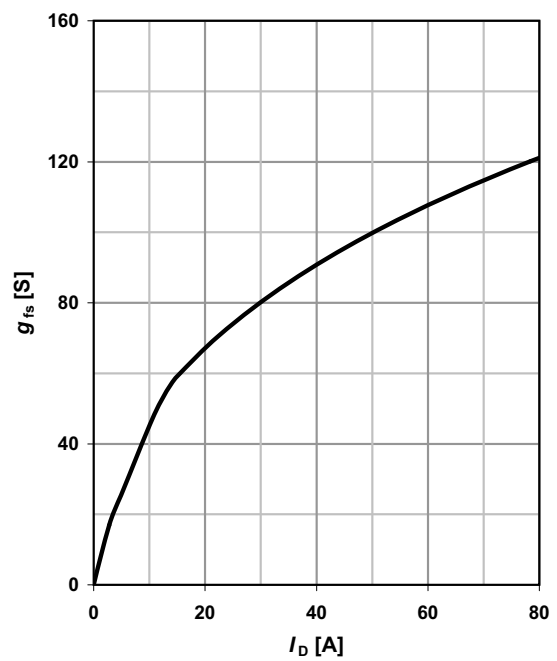
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



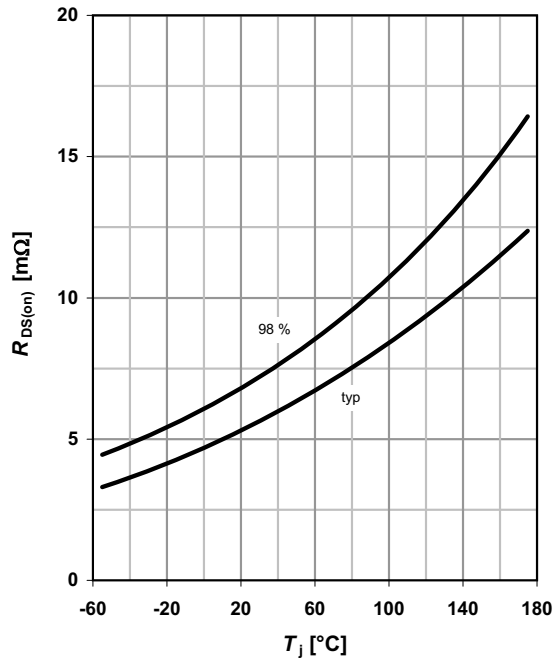
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



**9 Drain-source on-state resistance**

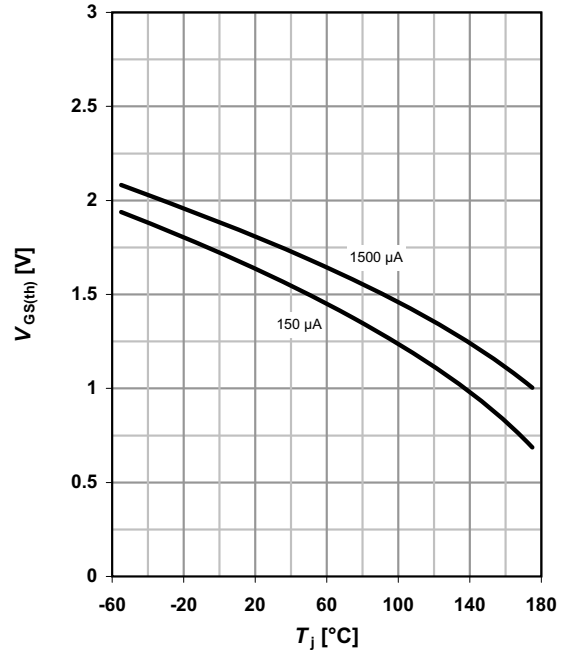
$R_{DS(on)} = f(T_j); I_D = 80 \text{ A}; V_{GS} = 10 \text{ V}$



**10 Typ. gate threshold voltage**

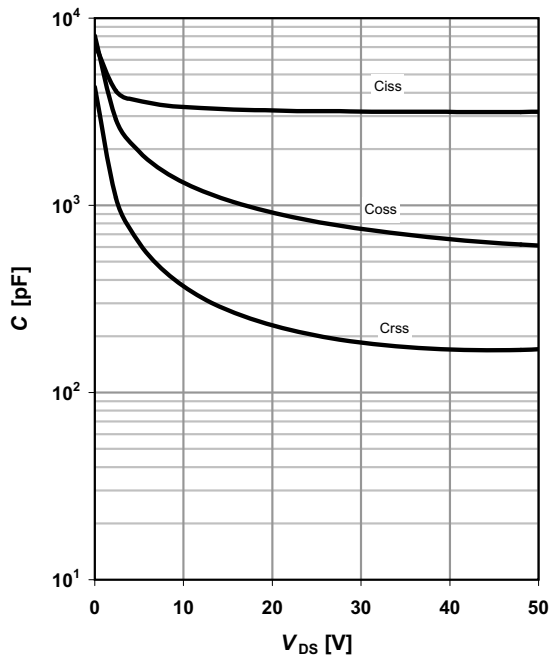
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

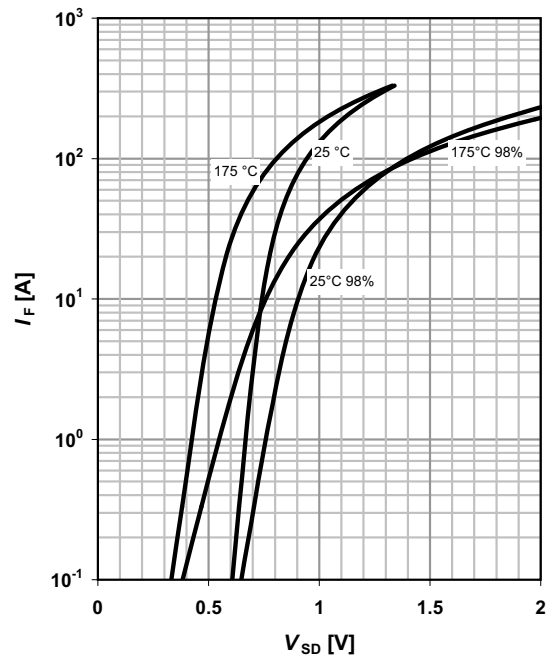
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

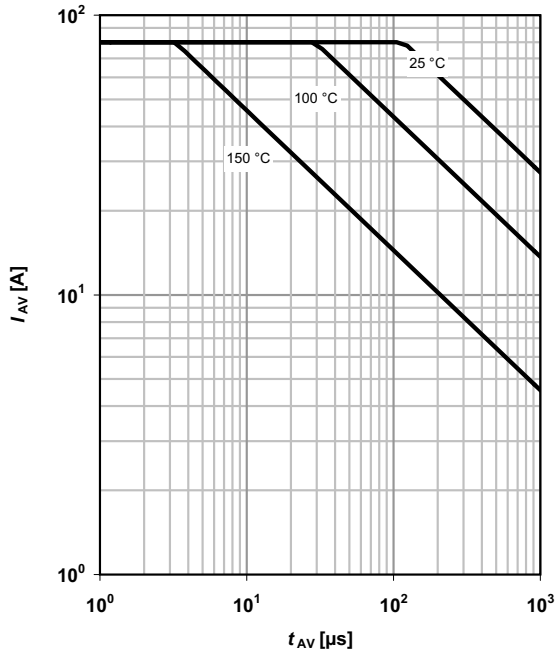
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

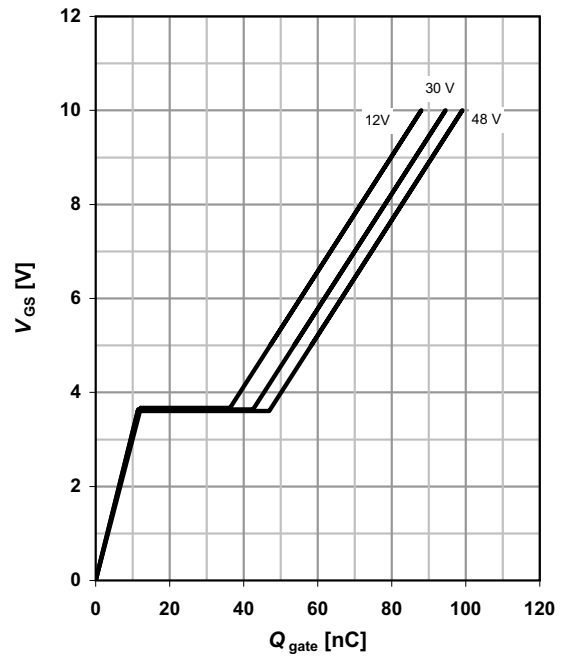
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

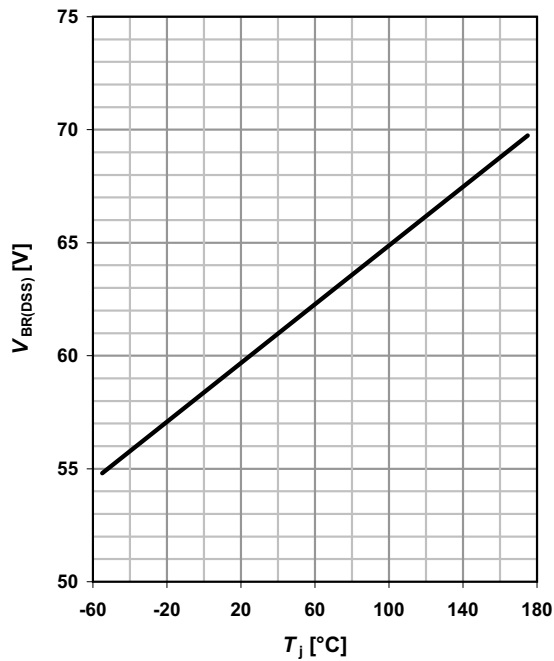
$V_{GS}=f(Q_{gate}); I_D=80 \text{ A pulsed}$

parameter:  $V_{DD}$

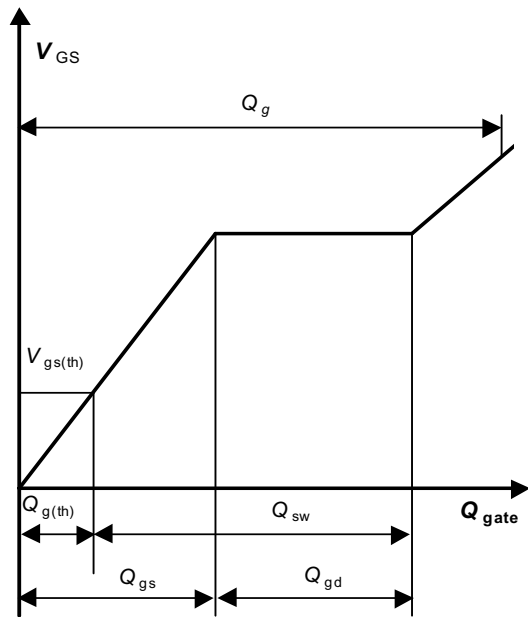


**15 Drain-source breakdown voltage**

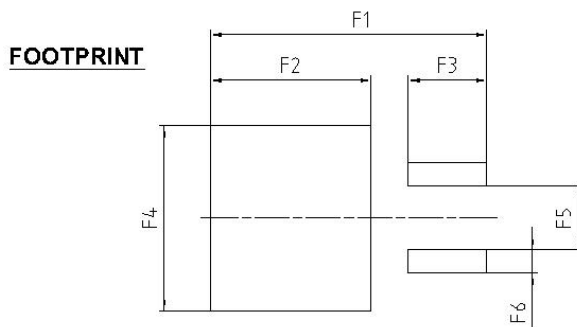
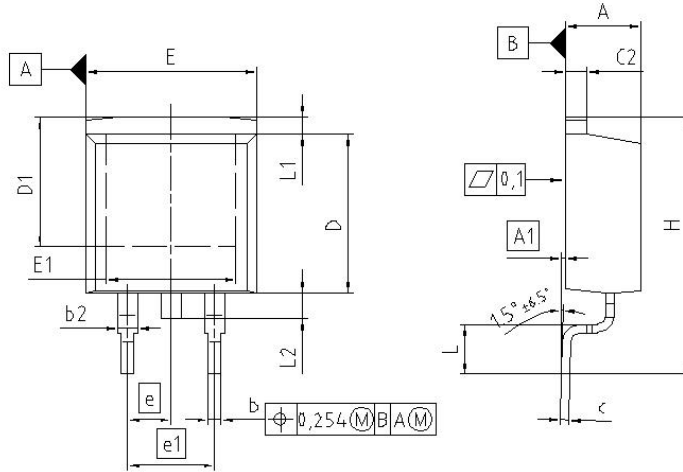
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



**16 Gate charge waveforms**



PG-TO-263-3 (D<sup>2</sup>-Pak)



| DIM | MILLIMETERS |        | INCHES |       |
|-----|-------------|--------|--------|-------|
|     | MIN         | MAX    | MIN    | MAX   |
| A   | 4.300       | 4.572  | 0.169  | 0.180 |
| A1  | 0.000       | 0.254  | 0.000  | 0.010 |
| b   | 0.650       | 0.850  | 0.026  | 0.033 |
| b2  | 0.950       | 1.321  | 0.037  | 0.052 |
| c   | 0.330       | 0.650  | 0.013  | 0.026 |
| c2  | 0.170       | 1.400  | 0.046  | 0.055 |
| D   | 8.509       | 9.450  | 0.335  | 0.372 |
| D1  | 7.100       | -      | 0.280  | -     |
| E   | 9.800       | 10.312 | 0.386  | 0.406 |
| E1  | 6.500       | -      | 0.256  | -     |
| e   | 2.540       |        | 0.100  |       |
| e1  | 5.080       |        | 0.200  |       |
| N   | 2           |        | 2      |       |
| H   | 14.605      | 15.875 | 0.575  | 0.625 |
| L   | 2.200       | 3.000  | 0.087  | 0.118 |
| L1  | -           | 1.600  | -      | 0.063 |
| L2  | 1.000       | 1.778  | 0.039  | 0.070 |
| F1  | 16.050      | 16.250 | 0.632  | 0.640 |
| F2  | 9.300       | 9.500  | 0.366  | 0.374 |
| F3  | 4.500       | 4.700  | 0.177  | 0.185 |
| F4  | 10.700      | 10.900 | 0.421  | 0.429 |
| F5  | 3.630       | 3.830  | 0.143  | 0.151 |
| F6  | 1.100       | 1.300  | 0.043  | 0.051 |

**REFERENCE**  
JEDEC TO263

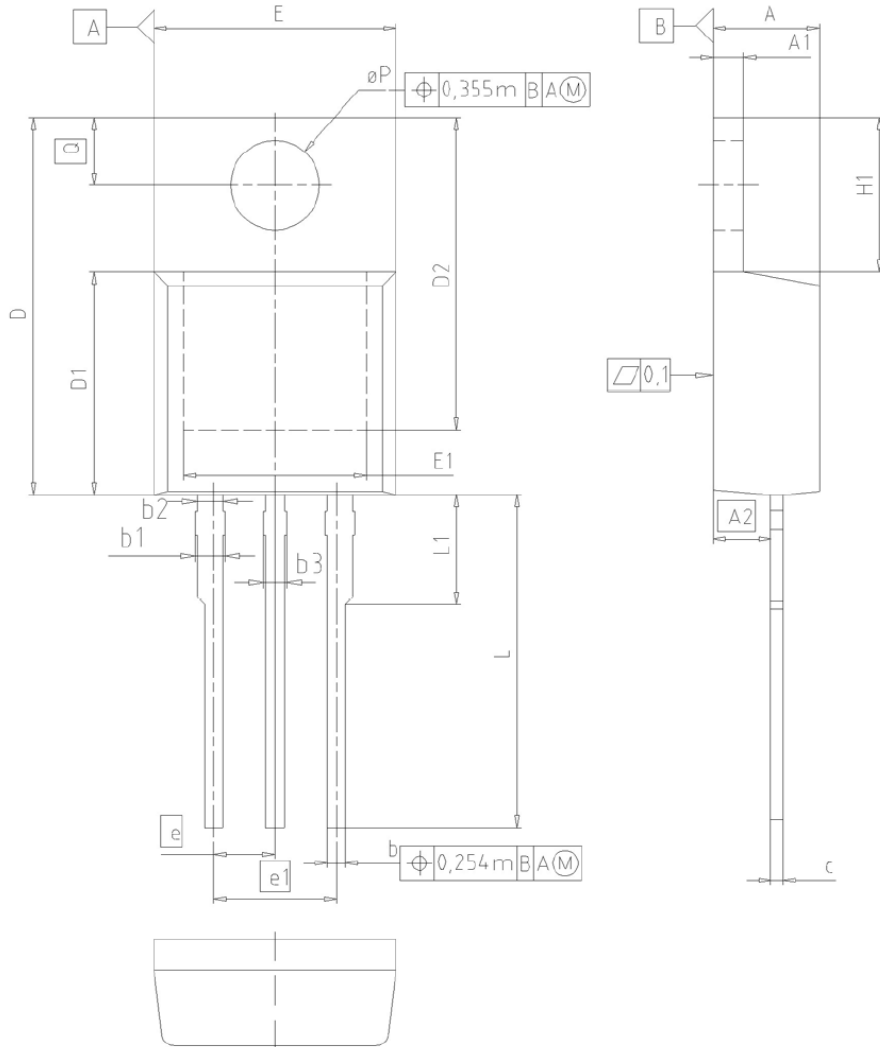
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**FILE**  
TO263\_2





| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.30        | 4.57  | 0.169  | 0.180 |
| A1  | 1.17        | 1.40  | 0.046  | 0.055 |
| A2  | 2.15        | 2.72  | 0.085  | 0.107 |
| b   | 0.65        | 0.86  | 0.026  | 0.034 |
| b1  | 0.95        | 1.40  | 0.037  | 0.055 |
| b2  | 0.95        | 1.15  | 0.037  | 0.045 |
| b3  | 0.65        | 1.15  | 0.026  | 0.045 |
| c   | 0.33        | 0.80  | 0.013  | 0.024 |
| D   | 14.81       | 15.95 | 0.583  | 0.628 |
| D1  | 8.51        | 9.45  | 0.335  | 0.372 |
| D2  | 12.19       | 13.10 | 0.480  | 0.516 |
| E   | 9.70        | 10.36 | 0.382  | 0.408 |
| E1  | 6.50        | 8.60  | 0.256  | 0.339 |
| e   | 2.54        |       | 0.100  |       |
| e1  | 5.08        |       | 0.200  |       |
| N   | 3           |       | 3      |       |
| H1  | 5.90        | 6.90  | 0.232  | 0.272 |
| L   | 13.00       | 14.00 | 0.512  | 0.551 |
| L1  | -           | 4.80  | -      | 0.189 |
| øP  | 3.60        | 3.89  | 0.142  | 0.153 |
| Q   | 2.60        | 3.00  | 0.102  | 0.118 |

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